27. A method for manufacturing a thin film transistor, comprising the steps of:

forming a semiconductor film on an insulating surface;

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface;

irradiating laser light to said semiconductor island; and

forming an insulating film on said semiconductor island.

28. A method for manufacturing a thin film transistor, comprising the steps of:

forming a semiconductor film on an insulating surface;

crystallizing said semiconductor film;

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface; and

irradiating laser light to said semiconductor island.

29. A method according to claim 26, wherein said patterning is performed by an isotropic dry etching method.

30. A method according to claim 27, wherein said patterning is performed by an isotropic dry etching method.

31. A method according to claim 28, wherein said patterning is performed by an isotropic dry etching method.

32. A method according to claim 26 further comprising the steps of forming a gate electrode on said insulating film.

33. A method according to claim 27 further comprising the steps of forming a gate electrode on said insulating film.